To our customers,

## Old Company Name in Catalogs and Other Documents

On April 1st, 2010, NEC Electronics Corporation merged with Renesas Technology Corporation, and Renesas Electronics Corporation took over all the business of both companies. Therefore, although the old company name remains in this document, it is a valid Renesas Electronics document. We appreciate your understanding.

Renesas Electronics website: http://www.renesas.com

April 1st, 2010
Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

Send any inquiries to http://www.renesas.com/inquiry.

# Notice

1. All information included in this document is current as of the date this document is issued. Such information, however, is subject to change without any prior notice. Before purchasing or using any Renesas Electronics products listed herein, please confirm the latest product information with a Renesas Electronics sales office. Also, please pay regular and careful attention to additional and different information to be disclosed by Renesas Electronics such as that disclosed through our website.
2. Renesas Electronics does not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Renesas Electronics products or technical information described in this document. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
3. You should not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part.
4. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits, software, or information.
5. When exporting the products or technology described in this document, you should comply with the applicable export control laws and regulations and follow the procedures required by such laws and regulations. You should not use Renesas Electronics products or the technology described in this document for any purpose relating to military applications or use by the military, including but not limited to the development of weapons of mass destruction. Renesas Electronics products and technology may not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations.
6. Renesas Electronics has used reasonable care in preparing the information included in this document, but Renesas Electronics does not warrant that such information is error free. Renesas Electronics assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein.
7. Renesas Electronics products are classified according to the following three quality grades: “Standard”, “High Quality”, and “Specific”. The recommended applications for each Renesas Electronics product depends on the product’s quality grade, as indicated below. You must check the quality grade of each Renesas Electronics product before using it in a particular application. You may not use any Renesas Electronics product for any application categorized as “Specific” without the prior written consent of Renesas Electronics. Further, you may not use any Renesas Electronics product for any application for which it is not intended without the prior written consent of Renesas Electronics. Renesas Electronics shall not be in any way liable for any damages or losses incurred by you or third parties arising from the use of any Renesas Electronics product for an application categorized as “Specific” or for which the product is not intended where you have failed to obtain the prior written consent of Renesas Electronics. The quality grade of each Renesas Electronics product is “Standard” unless otherwise expressly specified in a Renesas Electronics data sheets or data books, etc.

   “Standard”: Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; and industrial robots.

   “High Quality”: Transportation equipment (automobiles, trains, ships, etc.); traffic control systems; anti-disaster systems; anti-crime systems; safety equipment; and medical equipment not specifically designed for life support.

   “Specific”: Aircraft; aerospace equipment; submersible repeaters; nuclear reactor control systems; medical equipment or systems for life support (e.g. artificial life support devices or systems), surgical implantations, or healthcare intervention (e.g. excision, etc.), and any other applications or purposes that pose a direct threat to human life.
8. You should use the Renesas Electronics products described in this document within the range specified by Renesas Electronics, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. Renesas Electronics shall have no liability for malfunctions or damages arising out of the use of Renesas Electronics products beyond such specified ranges.
9. Although Renesas Electronics endeavors to improve the quality and reliability of its products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please be sure to implement safety measures to guard them against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas Electronics product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult, please evaluate the safety of the final products or system manufactured by you.
10. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please use Renesas Electronics products in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Renesas Electronics assumes no liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
11. This document may not be reproduced or duplicated, in any form, in whole or in part, without prior written consent of Renesas Electronics.
12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products, or if you have any other inquiries.

(Note 1) “Renesas Electronics” as used in this document means Renesas Electronics Corporation and also includes its majority-owned subsidiaries.

(Note 2) “Renesas Electronics product(s)” means any product developed or manufactured by or for Renesas Electronics.

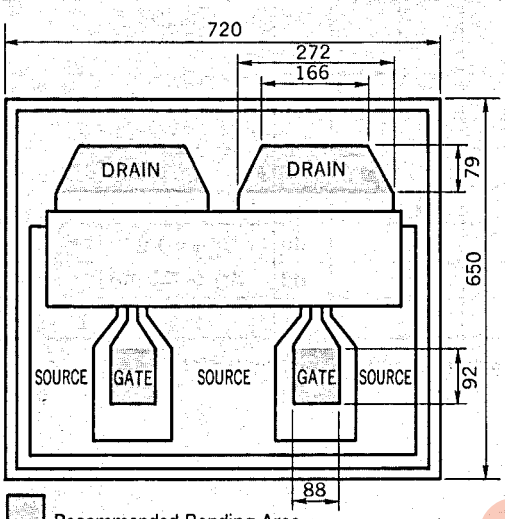
RENESAS

# GaAs MES FET
# NE8001

## C-BAND MEDIUM POWER GaAs FET
## N-CHANNEL GaAs MES FET

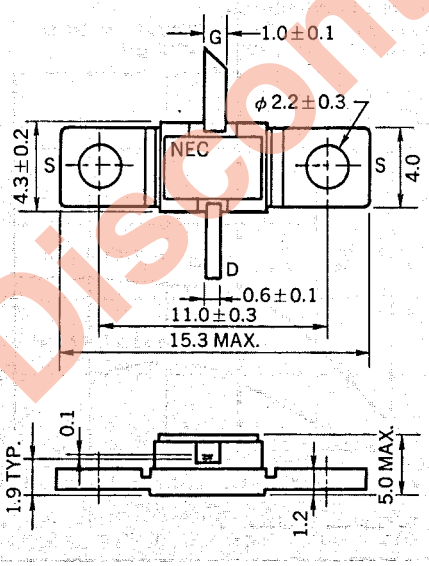


**PACKAGE DIMENSIONS**
**NE800100 (CHIP) *1**
(Units in mm)




Recommended Bonding Area.
Die Thickness: 110 to 160 $\mu$m

**PACKAGE CODE-96/99**
(Units in mm)




*1 The NE800100 has one good cell on two-cell chip. The waffle pack is marked with a circle to indicate which side of the chip has the good cell.

### DESCRIPTION

The NE8001 is a GaAs power FET offering a recessed gate structure which provides high break-down and operating voltages. The device operates with a drain voltage ($V_{DS}$) of 9 V for CW circuits and up to 13 V for pulsed circuits.

### FEATURES

- $P_{O(1\ dB)}$ = 26.0 dBm, $G_L$ = 9.5 dB @ $V_{DS}$ = 9 V
  f = 7.2 GHz (NE800196), 8.4 GHz (NE800199)
- Hermetically sealed package assures high reliability

### ORDERING INFORMATION

| PART NUMBER | PACKAGE CODE |
|---|---|
| NE800100 | 00(CHIP) |
| NE800196 | 96 |
| NE800199 | 99 |

### ABSOLUTE MAXIMUM RATING ($T_a$ = 25 °C)

| | | | |
|---|---|---|---|
| Drain to Source Voltage | $V_{DS}$ | 20 | V |
| Gate to Source Voltage | $V_{GS}$ | −14 | V |
| Drain Current | $I_D$ | 0.55 | A |
| Gate Current | $I_G$ | 1.5 | mA |
| Total Power Dissipation | $P_T$ | 2.5*2 | W |

*2 $T_c$ = 25 °C

## ELECTRICAL CHARACTERISTICS ($T_a$ = 25 °C)

| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS |
|---|---|---|---|---|---|---|
| Saturated Drain Current | $I_{DSS}$ | 225 | 300 | 400 | mA | $V_{DS}$ = 2.5 V, $V_{GS}$ = 0 |
| Pinch-off Voltage | $V_P$ | –2.5 | –3.5 | –5 | V | $V_{DS}$ = 2.5 V, $I_D$ = 2 mA |
| Transconductance | $g_m$ | | 60 | | mS | $V_{DS}$ = 3 V, $I_D$ = 100 mA |
| Thermal Resistance | $R_{th}$ | | 60 | 64 | °C/W | channel to case |

## PERFORMANCE SPECIFICATIONS ($T_a$ = 25 °C)

| PART NUMBER | | NE800100 | | | NE800196 | | | NE800199 | | | UNIT | TEST CONDITIONS | |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| PACKAGE CODE | | CHIP | | | 96 | | | 99 | | | | | |
| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. | | | |
| Output Power*3 | $P_{out}$ | 25 | 26 | | 25 | 26 | | | | | dBm | $V_{DS}$ = 9 V, $I_D \leqq$ 150 mA | $P_{in}$ = 17.5 dBm, f = 7.2 GHz |
| | | | | | | | | 25 | 26 | | dBm | | $P_{in}$ = 18.0 dBm, f = 8.4 GHz |
| Output Power at 1 dB Gain Compression Point | $P_{O(1\ dB)}$ | | 26 | | | 26 | | | | | dBm | $V_{DS}$ = 9 V, $I_D \leqq$ 125 mA | f = 7.2 GHz |
| | | | | | | | | | 26 | | dBm | | f = 8.4 GHz |
| Linear Gain | $G_L$ | | 9.5 | | | 9.5 | | | | | dB | $V_{DS}$ = 9 V, $I_D \leqq$ 125 mA | f = 7.2 GHz |
| | | | | | | | | | 9.5 | | dB | | f = 8.4 GHz |
| Power Added Efficiency*4 | $\eta_{add}$ | | 38 | | | 38 | | | 38 | | % | $P_{out} = P_{O(1\ dB)}$ | |

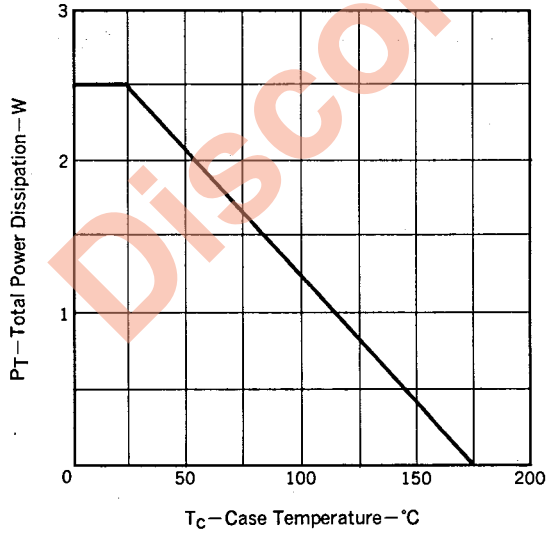
*3 Devices are measured in a tuned amplifier circuit. The drain current $I_D$ is 100 to 150 mA and the gate current is limited below the absolute maximum rating.

*4 $\eta_{add} = \dfrac{P_{O(1\ dB)} - P_{in}}{V_{DS} \times I_D} \times 100\ (\%)$

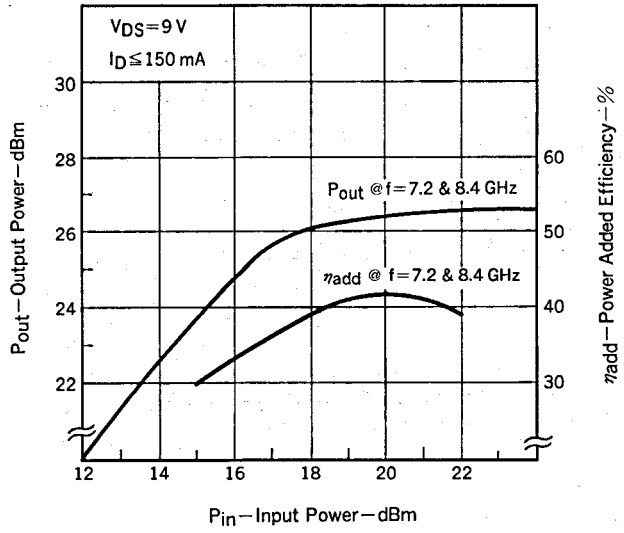


## TYPICAL CHARACTERISTICS ($T_a$ = 25 °)

POWER DERATING CURVE




NE800196, NE800199
OUTPUT POWER AND POWER ADDED EFFICIENCY vs. INPUT POWER



## NE800100 S-PARAMETER ($V_{DS}$ = 9 V, $I_D$ = 150 mA)

| frequency (MHz) | $S_{11}$ | | $S_{21}$ | | $S_{12}$ | | $S_{22}$ | |
|---|---|---|---|---|---|---|---|---|
| 1000 | 0.934 | –64.1 | 4.951 | 137.3 | 0.046 | 55.9 | 0.509 | –24.3 |
| 2000 | 0.859 | –107.1 | 3.575 | 108.0 | 0.065 | 34.6 | 0.413 | –41.1 |
| 3000 | 0.828 | –134.0 | 2.674 | 89.3 | 0.072 | 24.0 | 0.383 | –48.3 |
| 4000 | 0.811 | –151.2 | 2.108 | 73.6 | 0.073 | 16.6 | 0.381 | –59.6 |
| 5000 | 0.806 | –163.0 | 1.728 | 60.9 | 0.072 | 14.0 | 0.389 | –70.0 |
| 6000 | 0.801 | –172.9 | 1.454 | 49.2 | 0.069 | 10.2 | 0.399 | –80.1 |
| 7000 | 0.792 | 179.4 | 1.250 | 39.4 | 0.057 | 15.5 | 0.417 | –87.8 |
| 8000 | 0.803 | 171.7 | 1.109 | 29.2 | 0.098 | 21.3 | 0.419 | –100.3 |
| 9000 | 0.813 | 166.1 | 0.996 | 19.0 | 0.071 | 8.3 | 0.469 | –106.4 |
| 10000 | 0.818 | 160.8 | 0.893 | 9.5 | 0.070 | 9.7 | 0.504 | –116.5 |
| 11000 | 0.812 | 155.1 | 0.814 | 0.3 | 0.070 | 11.0 | 0.537 | –123.6 |
| 12000 | 0.804 | 148.5 | 0.727 | –9.5 | 0.070 | 12.1 | 0.567 | –131.1 |
| 13000 | 0.810 | 142.2 | 0.657 | –18.1 | 0.073 | 13.7 | 0.597 | –138.3 |
| 14000 | 0.820 | 137.4 | 0.592 | –26.2 | 0.074 | 14.3 | 0.623 | –145.9 |
| 15000 | 0.821 | 134.4 | 0.532 | –33.7 | 0.074 | 19.6 | 0.650 | –151.7 |
| 16000 | 0.809 | 130.1 | 0.489 | –42.0 | 0.085 | 20.8 | 0.677 | –156.8 |
| 17000 | 0.781 | 124.3 | 0.438 | –49.1 | 0.098 | 22.2 | 0.685 | –163.8 |
| 18000 | 0.777 | 118.2 | 0.405 | –56.9 | 0.111 | 14.7 | 0.697 | –173.1 |

## NE800196 S-PARAMETER ($V_{DS}$ = 9 V, $I_D$ = 150 mA)

| frequency (MHz) | $S_{11}$ | | $S_{21}$ | | $S_{12}$ | | $S_{22}$ | |
|---|---|---|---|---|---|---|---|---|
| 1000 | 0.898 | –108.7 | 4.492 | 104.8 | 0.045 | 32.1 | 0.402 | –45.9 |
| 2000 | 0.851 | –152.8 | 2.816 | 64.7 | 0.052 | 11.1 | 0.362 | –77.8 |
| 3000 | 0.825 | –175.6 | 2.160 | 35.0 | 0.053 | 2.2 | 0.385 | –110.2 |
| 4000 | 0.786 | 168.3 | 1.973 | 7.5 | 0.051 | –1.4 | 0.458 | –135.5 |
| 5000 | 0.678 | 149.4 | 2.167 | –24.6 | 0.063 | –10.6 | 0.567 | –158.3 |
| 6000 | 0.214 | 123.0 | 2.707 | –77.9 | 0.069 | –50.9 | 0.745 | 174.4 |
| 7000 | 0.654 | –142.0 | 1.846 | –154.3 | 0.019 | –154.0 | 0.692 | 137.5 |
| 8000 | 0.877 | –171.8 | 0.880 | 157.8 | 0.041 | 66.9 | 0.588 | 118.6 |
| 9000 | 0.897 | 170.9 | 0.485 | 120.9 | 0.069 | 34.5 | 0.545 | 100.6 |
| 10000 | 0.879 | 156.8 | 0.310 | 85.0 | 0.092 | 13.9 | 0.525 | 83.0 |

## NE800199 S-PARAMETER ($V_{DS}$ = 9 V, $I_D$ = 150 mA)

| frequency (MHz) | $S_{11}$ | | $S_{21}$ | | $S_{12}$ | | $S_{22}$ | |
|---|---|---|---|---|---|---|---|---|
| 1000 | 0.903 | –88.5 | 4.972 | 114.8 | 0.037 | 40.4 | 0.462 | –42.3 |
| 2000 | 0.815 | –140.0 | 3.323 | 71.8 | 0.045 | 17.0 | 0.418 | –75.2 |
| 3000 | 0.799 | –169.4 | 2.497 | 40.3 | 0.042 | 9.6 | 0.425 | –107.8 |
| 4000 | 0.788 | 169.1 | 2.070 | 12.4 | 0.041 | 13.2 | 0.485 | –135.0 |
| 5000 | 0.766 | 149.0 | 1.886 | –14.0 | 0.051 | 16.7 | 0.545 | –158.3 |
| 6000 | 0.708 | 124.0 | 1.878 | –42.8 | 0.065 | 5.9 | 0.625 | –179.0 |
| 7000 | 0.588 | 83.6 | 1.998 | –78.4 | 0.074 | –17.3 | 0.696 | 158.9 |
| 8000 | 0.457 | 10.1 | 2.005 | –124.2 | 0.059 | –60.0 | 0.776 | 133.1 |
| 9000 | 0.551 | –77.3 | 1.666 | –177.3 | 0.028 | 173.4 | 0.760 | 102.2 |
| 10000 | 0.642 | –132.2 | 1.193 | 135.9 | 0.084 | 85.2 | 0.680 | 77.1 |

## CHIP HANDLING

### DIE ATTACHEMENT

Die attach can be accomplished with a Au-Sn (300 ± 10 °C) preforms in a forming gas environment. Epoxy die attach is not recommended.

### BONDING

Gate and drain bonding wires should be minimum length, semi-hard gold wire (3-8 % elongation) 30 microns or less in diameter. Bonding should be performed with a wedge tip that has a taper of approximately 15 %. Die attach and bonding time should be kept to a minimum. As a general rule, the bonding operation should be kept within a 280 °C — 5 minute curve. If longer periods are required, the temperature should be lowered.

### PRECAUTIONS

The user must operate in a clean, dry environment. The chip channel is glassivated for mechanical protection only and does not preclude the necessity of a clean environment.

The bonding equipment should be periodically checked for sources of surge voltage and should be properly grounded at all times. In fact, all test and handling equipment should be grounded to minimize the possibilities of static discharge.



TC—1910
September 1987M
Printed in Japan